

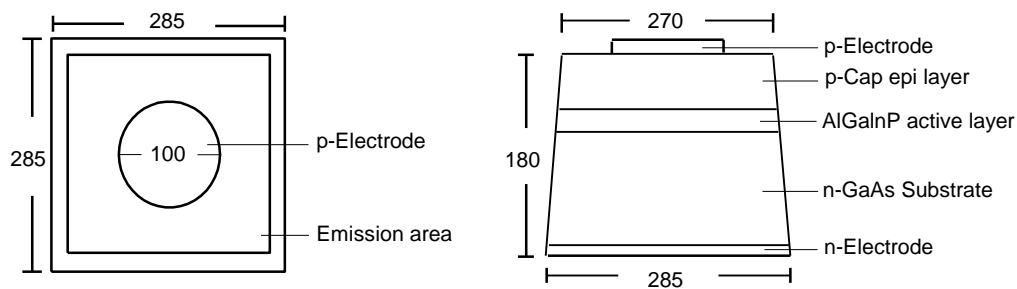
■ **Features :**

- MOVPE epi wafer
- Suitable for new creative products

■ **Typical Applications :**

- SMD Chip LED
- Backlight
- Equipment indicators
- Message Boards
- Commercial Applications

■ **Outline Dimensions : (Unit: um)**



■ **Physical Structure :**

Chip dimension	Chip size	285 um x 285um
	Thickness	180 um
	Emission area	270 um
	Bonding pad	100 um
Electrode	Top: P (anode)	Gold (Aluminum optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

■ **Electro-Optical Characteristics : (Ta = 25°C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 20 \text{ mA}$	-	2.05	2.40	V
Reverse Voltage	$V_R$	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	$\lambda_P$	$I_F = 20 \text{ mA}$	-	-	-	nm
	$\lambda_d$		589	594	599	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	20	-	nm
Luminous Intensity	$I_v$	$I_F = 20 \text{ mA}$	240	-	-	mcd

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

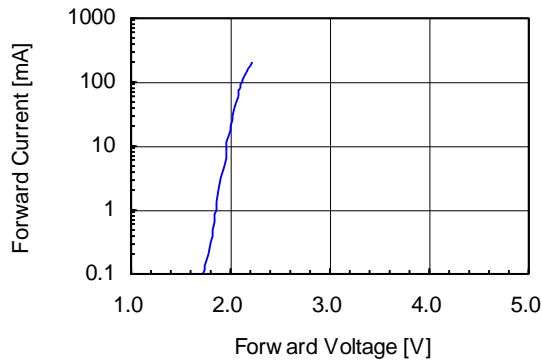


Fig 2. Relative Intensity vs. Forward Current

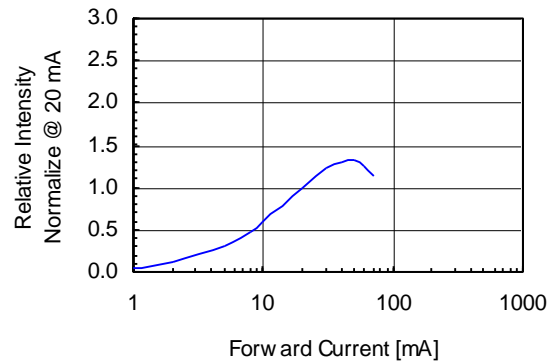


Fig 3. Forward Voltage vs. Temperature

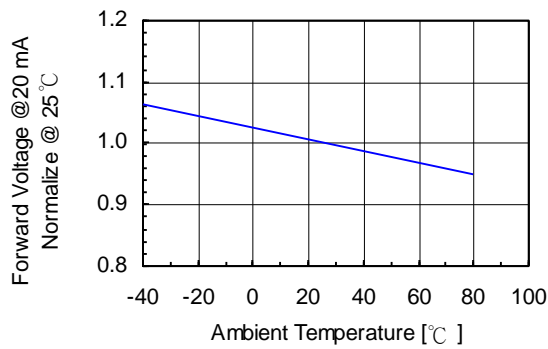


Fig 4. Relative Intensity vs. Temperature

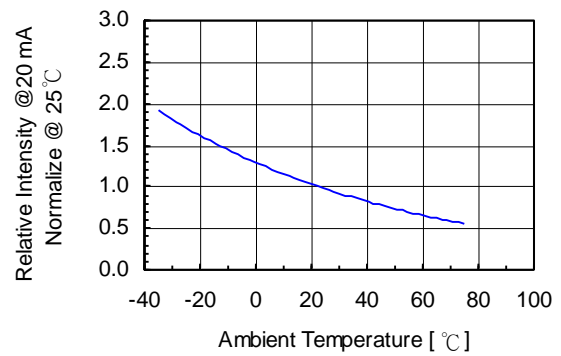


Fig 5. Relative Intensity vs. Wavelength

